

# Wei-Hua Wang

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

47  
papers

1,521  
citations

20  
h-index

38  
g-index

49  
ext. papers

1,727  
ext. citations

7.2  
avg, IF

4.08  
L-index

#	Paper	IF	Citations
47	Magnetotransport in hybrid InSe/monolayer graphene on SiC. <i>Nanotechnology</i> , <b>2021</b> , 32, 155704	3.4	1
46	Self-Sufficient and Highly Efficient Gold Sandwich Upconversion Nanocomposite Lasers for Stretchable and Bio-applications. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2020</b> , 12, 19840-19854	9.5	10
45	Ultrahighly Photosensitive and Highly Stretchable Rippled Structure Photodetectors Based on Perovskite Nanocrystals and Graphene. <i>ACS Applied Electronic Materials</i> , <b>2019</b> , 1, 1517-1526	4	3
44	Oxidized-monolayer tunneling barrier for strong Fermi-level depinning in layered InSe transistors. <i>Npj 2D Materials and Applications</i> , <b>2019</b> , 3,	8.8	8
43	Transparent, Wearable, Broadband, and Highly Sensitive Upconversion Nanoparticles and Graphene-Based Hybrid Photodetectors. <i>ACS Photonics</i> , <b>2018</b> , 5, 2336-2347	6.3	38
42	Spatially and Precisely Controlled Large-Scale and Persistent Optical Gating in a TiO <sub>2</sub> -MoS <sub>2</sub> Heterostructure. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 38319-38325	9.5	0
41	Highly Sensitive, Visible Blind, Wearable, and Omnidirectional Near-Infrared Photodetectors. <i>ACS Nano</i> , <b>2018</b> , 12, 9596-9607	16.7	31
40	High-Performance InSe Transistors with Ohmic Contact Enabled by Nonrectifying Barrier-Type Indium Electrodes. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 33450-33456	9.5	20
39	Probing the optical characteristics of MoS <sub>2</sub> under external electrical fields using polarized Raman spectroscopy. <i>Journal Physics D: Applied Physics</i> , <b>2018</b> , 51, 385303	3	3
38	Environment-insensitive and gate-controllable photocurrent enabled by bandgap engineering of MoS <sub>2</sub> junctions. <i>Scientific Reports</i> , <b>2017</b> , 7, 44768	4.9	10
37	Surface Oxidation Doping to Enhance Photogenerated Carrier Separation Efficiency for Ultrahigh Gain Indium Selenide Photodetector. <i>ACS Photonics</i> , <b>2017</b> , 4, 2930-2936	6.3	34
36	Influence of Oxygen Vacancies on the Frictional Properties of Nanocrystalline Zinc Oxide Thin Films in Ambient Conditions. <i>Langmuir</i> , <b>2017</b> , 33, 8362-8371	4	6
35	High-Mobility InSe Transistors: The Role of Surface Oxides. <i>ACS Nano</i> , <b>2017</b> , 11, 7362-7370	16.7	132
34	Nonlinear bandgap opening behavior of BN co-doped graphene. <i>Carbon</i> , <b>2016</b> , 107, 857-864	10.4	21
33	Observation of quantum Hall plateau-plateau transition and scaling behavior of the zeroth Landau level in graphene p-n junctions. <i>Physical Review B</i> , <b>2016</b> , 93,	3.3	4
32	Tunable Photoinduced Carrier Transport of a Black Phosphorus Transistor with Extended Stability Using a Light-Sensitized Encapsulated Layer. <i>ACS Photonics</i> , <b>2016</b> , 3, 1102-1108	6.3	16
31	Understanding the Interplay between Molecule Orientation and Graphene Using Polarized Raman Spectroscopy. <i>ACS Photonics</i> , <b>2016</b> , 3, 985-991	6.3	10

30	Extrinsic Origin of Persistent Photoconductivity in Monolayer MoS <sub>2</sub> Field Effect Transistors. <i>Scientific Reports</i> , <b>2015</b> , 5, 11472	4.9	94
29	Precisely Controlled Ultrastrong Photoinduced Doping at Graphene-Heterostructures Assisted by Trap-State-Mediated Charge Transfer. <i>Advanced Materials</i> , <b>2015</b> , 27, 7809-15	24	34
28	Demonstration of distinct semiconducting transport characteristics of monolayer graphene functionalized via plasma activation of substrate surfaces. <i>Carbon</i> , <b>2015</b> , 93, 353-360	10.4	5
27	Probing substrate influence on graphene by analyzing Raman lineshapes. <i>Nanoscale Research Letters</i> , <b>2014</b> , 9, 64	5	3
26	Probing 2D sub-bands of bi-layer graphene. <i>RSC Advances</i> , <b>2014</b> , 4, 51067-51071	3.7	4
25	Transport in disordered monolayer MoS <sub>2</sub> nanoflakes--evidence for inhomogeneous charge transport. <i>Nanotechnology</i> , <b>2014</b> , 25, 375201	3.4	23
24	Residue-free fabrication of high-performance graphene devices by patterned PMMA stencil mask. <i>AIP Advances</i> , <b>2014</b> , 4, 067129	1.5	9
23	Revealing anisotropic strain in exfoliated graphene by polarized Raman spectroscopy. <i>Nanoscale</i> , <b>2013</b> , 5, 9626-32	7.7	13
22	Biologically inspired graphene-chlorophyll phototransistors with high gain. <i>Carbon</i> , <b>2013</b> , 63, 23-29	10.4	83
21	Surface-enhanced Raman scattering of suspended monolayer graphene. <i>Nanoscale Research Letters</i> , <b>2013</b> , 8, 480	5	7
20	Spin transport and relaxation in graphene. <i>Journal of Magnetism and Magnetic Materials</i> , <b>2012</b> , 324, 369-381	3.8	112
19	Observation of strain effect on the suspended graphene by polarized Raman spectroscopy. <i>Nanoscale Research Letters</i> , <b>2012</b> , 7, 533	5	14
18	Layer-dependent morphologies of silver on n-layer graphene. <i>Nanoscale Research Letters</i> , <b>2012</b> , 7, 618	5	12
17	Transport/magnetotransport of high-performance graphene transistors on organic molecule-functionalized substrates. <i>Nano Letters</i> , <b>2012</b> , 12, 964-9	11.5	54
16	Self-encapsulated doping of n-type graphene transistors with extended air stability. <i>ACS Nano</i> , <b>2012</b> , 6, 6215-21	16.7	65
15	High-quality graphene p-n junctions via resist-free fabrication and solution-based noncovalent functionalization. <i>ACS Nano</i> , <b>2011</b> , 5, 2051-9	16.7	111
14	Oxidation-induced biquadratic coupling in Co/Fe/MgO/Fe(001). <i>Physical Review B</i> , <b>2009</b> , 79,	3.3	19
13	Electrical detection of spin precession in single layer graphene spin valves with transparent contacts. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 222109	3.4	122

12	Spin transport in graphite and graphene spin valves <b>2009</b> ,		7
11	Electron-hole asymmetry of spin injection and transport in single-layer graphene. <i>Physical Review Letters</i> , <b>2009</b> , 102, 137205	7-4	113
10	Efficient Numerical Schemes for Electronic States in Coupled Quantum Dots. <i>Journal of Nanoscience and Nanotechnology</i> , <b>2008</b> , 8, 3695-3709	1-3	28
9	Growth of atomically smooth MgO films on graphene by molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 183107	3-4	40
8	Magnetotransport properties of mesoscopic graphite spin valves. <i>Physical Review B</i> , <b>2008</b> , 77,	3-3	98
7	Inversion of ferromagnetic proximity polarization by MgO interlayers. <i>Physical Review Letters</i> , <b>2008</b> , 100, 237205	7-4	13
6	Enhancement of spin coherence using Q-factor engineering in semiconductor microdisc lasers. <i>Nature Materials</i> , <b>2006</b> , 5, 261-4	27	53
5	Fabrication and Characterization of Modulation-Doped ZnSe/(Zn,Cd)Se (110) Quantum Wells: A New System for Spin Coherence Studies. <i>Journal of Superconductivity and Novel Magnetism</i> , <b>2005</b> , 18, 185-188		4
4	Static and dynamic spectroscopy of (Al,Ga)As/GaAs microdisk lasers with interface fluctuation quantum dots. <i>Physical Review B</i> , <b>2005</b> , 71,	3-3	21
3	Exciton localization in Mg <sub>x</sub> Zn <sub>y</sub> Cd <sub>1-x-y</sub> Se alloy. <i>Physica Status Solidi (B): Basic Research</i> , <b>2004</b> , 241, 495-498	1-3	4
2	Temperature dependence of the energy gap of Mg <sub>x</sub> Zn <sub>y</sub> Cd <sub>1-x-y</sub> Se alloy. <i>Physica Status Solidi (B): Basic Research</i> , <b>2004</b> , 241, R5-R7	1-3	2
1	Optical properties of Zn <sub>0.5</sub> Cd <sub>0.5</sub> Se thin films grown on InP by molecular beam epitaxy. <i>Solid State Communications</i> , <b>2003</b> , 128, 461-466	1-6	7